Technical Data
DIODE

DISCRETE SEMICONDUCTOR INDUSTRIES

maximum ratings

Voltage, Reverse (VR)	1000.0	V
Voltage, Reverse Peak (VRM)	1000.0	V
Current at VR = OV (IO)		A
Current Average Rectified (IF)	12.0	A
Current Surge Peak (IZM)		A
Current, Surge (IFM) at tp = 8.3 ms	240.0	A
Max. Power Dissipation (PT) at TC = °C		W
Max. Thermal Resistance (Rth J-C)	2.0	°C/W
Max. Junction Temperature (TJ)	150.0	°C

NO.	1N3673A
TYPE	SILICON
CASE	DO-4_UNF
	CATHODE TO STUD

PERFORMANCE CHARACTERISTICS at T_C = 25°C, unless otherwise noted

NO.	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
1.	IR	VR = 1000.0 V	-	50.0	µA
2.	IR	VR = 1000.0 V, TJ = 125.0° C	-	1.0	mA
3.	VF	IF = 12.0 A (1)	-	1.1	V
4.	trr	IF = 1.0 A, VR = 30.0 V	-	5.0	µs
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6.					
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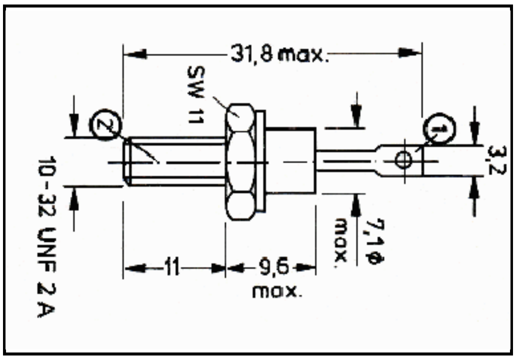
15.					
16.					
17.					
18.					
19.					
20.					

Notes (1)pulse-tested tp ≤ 300 µs, duty cycle ≤ 2 %

DIMENSIONS
in mm



Marking 1N3673A

Customer GENERAL PURPOSE